ON Semiconductor®

FDMC2514SDC

N-Channel Dual Cool™ 33 PowerTrench® SyncFET™

25 V, 40 A, 3.5 mΩ

Features

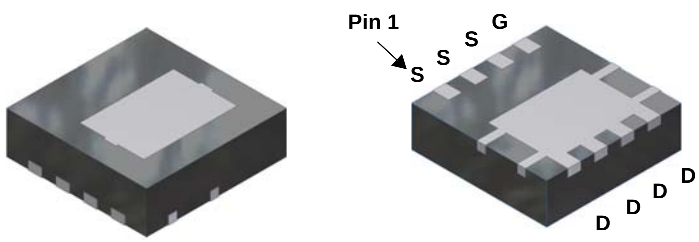
- Dual Cool™ Top Side Cooling PQFN package
- Max $r_{DS(on)}$ = 3.5 mΩ at V_{GS} = 10 V, I_D = 22.5 A
- Max $r_{DS(on)}$ = 4.7 mΩ at V_{GS} = 4.5 V, I_D = 18 A
- High performance technology for extremely low $r_{DS(on)}$
- SyncFET Schottky Body Diode
- RoHS Compliant

General Description

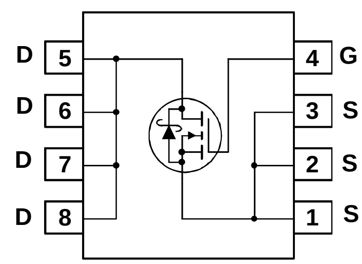
This N-Channel MOSFET is produced using ON Semiconductor's advanced PowerTrench® process. Advancements in both silicon and Dual Cool™ package technologies have been combined to offer the lowest $r_{DS(on)}$ while maintaining excellent switching performance by extremely low Junction-to-Ambient thermal resistance. This device has the added benefit of an efficient monolithic Schottky body diode.

Applications

- Synchronous Rectifier for DC/DC Converters
- Telecom Secondary Side Rectification
- High End Server/Workstation Vcore Low Side



Top   Dual Cool™ 33   Bottom



MOSFET Maximum Ratings T_A = 25°C unless otherwise noted

Symbol	Parameter	Ratings	Units
V_{DS}	Drain to Source Voltage	25	V
V_{GS}	Gate to Source Voltage (Note 4)	±20	V
I_D	Drain Current -Continuous (Package limited) T_C = 25 °C	40	A
	-Continuous (Silicon limited) T_C = 25 °C	106	
	-Continuous T_A = 25 °C (Note 1a)	24	
	-Pulsed	200	
E_{AS}	Single Pulse Avalanche Energy (Note 3)	84	mJ
dv/dt	Peak Diode Recovery dv/dt (Note 5)	2.0	V/ns
P_D	Power Dissipation T_C = 25 °C	60	W
	Power Dissipation T_A = 25 °C (Note 1a)	3.0	
T_J, T_{STG}	Operating and Storage Junction Temperature Range	-55 to +150	°C

Thermal Characteristics

$R_{\theta JC}$	Thermal Resistance, Junction to Case (Top Source)	5.8	°C/W
$R_{\theta JC}$	Thermal Resistance, Junction to Case (Bottom Drain)	2.1	
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient (Note 1a)	42	
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient (Note 1b)	105	
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient (Note 1i)	17	
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient (Note 1j)	26	
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient (Note 1k)	12	

Package Marking and Ordering Information

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
2514S	FDMC2514SDC	Dual Cool™ 33	13''	12 mm	3000 units

Electrical Characteristics T_J = 25 °C unless otherwise noted

Off Characteristics

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
BV_{DSS}	Drain to Source Breakdown Voltage	I_D = 1 mA, V_{GS} = 0 V	25			V
$\frac{\Delta BV_{DSS}}{\Delta T_J}$	Breakdown Voltage Temperature Coefficient	I_D = 10 mA, referenced to 25 °C		21		mV/°C
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS} = 20 V, V_{GS} = 0 V			500	μA
I_{GSS}	Gate to Source Leakage Current, Forward	V_{GS} = 20 V, V_{DS} = 0 V			100	nA

On Characteristics

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
$V_{GS(th)}$	Gate to Source Threshold Voltage	V_{GS} = V_{DS}, I_D = 1 mA	1.2	1.7	3.0	V
$\frac{\Delta V_{GS(th)}}{\Delta T_J}$	Gate to Source Threshold Voltage Temperature Coefficient	I_D = 10 mA, referenced to 25 °C		-5		mV/°C
$r_{DS(on)}$	Static Drain to Source On Resistance	V_{GS} = 10 V, I_D = 22.5 A		2.5	3.5	mΩ
		V_{GS} = 4.5 V, I_D = 18 A		3.6	4.7	
		V_{GS} = 10 V, I_D = 22.5 A, T_J = 125 °C		3.5	4.5	
g_{FS}	Forward Transconductance	V_{DS} = 5 V, I_D = 22.5 A		122		S

Dynamic Characteristics

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
C_{iss}	Input Capacitance	V_{DS} = 13 V, V_{GS} = 0 V, f = 1 MHz		2031	2705	pF
C_{oss}	Output Capacitance			596	795	pF
C_{rss}	Reverse Transfer Capacitance			134	205	pF
R_g	Gate Resistance			1.1	2.4	Ω

Switching Characteristics

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
$t_{d(on)}$	Turn-On Delay Time	V_{DD} = 13 V, I_D = 22.5 A, V_{GS} = 10 V, R_{GEN} = 6 Ω		11	22	ns
t_r	Rise Time			3.6	10	ns
$t_{d(off)}$	Turn-Off Delay Time			26	41	ns
t_f	Fall Time			3	10	ns
Q_g	Total Gate Charge	V_{GS} = 0 V to 10 V; V_{DD} = 13 V, I_D = 22.5 A		31	44	nC
Q_g	Total Gate Charge	V_{GS} = 0 V to 4.5 V		14	20	nC
Q_{gs}	Gate to Source Gate Charge			6.5		nC
Q_{gd}	Gate to Drain “Miller” Charge			3.9		nC

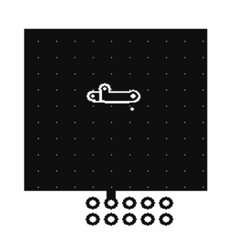
Drain-Source Diode Characteristics

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
V_{SD}	Source to Drain Diode Forward Voltage	V_{GS} = 0 V, I_S = 22.5 A (Note 2)		0.79	1.2	V
		V_{GS} = 0 V, I_S = 2 A (Note 2)		0.47	0.8	
t_{rr}	Reverse Recovery Time	I_F = 22.5 A, di/dt = 300 A/μs		24	39	ns
Q_{rr}	Reverse Recovery Charge			19	34	nC

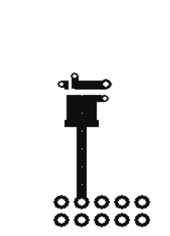
Thermal Characteristics

$R_{\theta JC}$	Thermal Resistance, Junction to Case	(Top Source)	5.8	°C/W
$R_{\theta JC}$	Thermal Resistance, Junction to Case	(Bottom Drain)	2.1	
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	(Note 1a)	42	
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	(Note 1b)	105	
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	(Note 1c)	29	
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	(Note 1d)	40	
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	(Note 1e)	19	
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	(Note 1f)	23	
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	(Note 1g)	30	
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	(Note 1h)	79	
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	(Note 1i)	17	
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	(Note 1j)	26	
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	(Note 1k)	12	
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	(Note 1l)	16	

NOTES:
1. $R_{\theta JA}$ is determined with the device mounted on a FR-4 board using a specified pad of 2 oz copper as shown below. $R_{\theta JC}$ is guaranteed by design while $R_{\theta CA}$ is determined by the user's board design.



a. 42 °C/W when mounted on a 1 in^2 pad of 2 oz copper



b. 105 °C/W when mounted on a minimum pad of 2 oz copper

c. Still air, 20.9x10.4x12.7mm Aluminum Heat Sink, 1 in^2 pad of 2 oz copper

d. Still air, 20.9x10.4x12.7mm Aluminum Heat Sink, minimum pad of 2 oz copper

e. Still air, 45.2x41.4x11.7mm Aavid Thermalloy Part # 10-L41B-11 Heat Sink, 1 in^2 pad of 2 oz copper

f. Still air, 45.2x41.4x11.7mm Aavid Thermalloy Part # 10-L41B-11 Heat Sink, minimum pad of 2 oz copper

g. 200FPM Airflow, No Heat Sink,1 in^2 pad of 2 oz copper

h. 200FPM Airflow, No Heat Sink, minimum pad of 2 oz copper

i. 200FPM Airflow, 20.9x10.4x12.7mm Aluminum Heat Sink, 1 in^2 pad of 2 oz copper

j. 200FPM Airflow, 20.9x10.4x12.7mm Aluminum Heat Sink, minimum pad of 2 oz copper

k. 200FPM Airflow, 45.2x41.4x11.7mm Aavid Thermalloy Part # 10-L41B-11 Heat Sink, 1 in^2 pad of 2 oz copper

l. 200FPM Airflow, 45.2x41.4x11.7mm Aavid Thermalloy Part # 10-L41B-11 Heat Sink, minimum pad of 2 oz copper

2. Pulse Test: Pulse Width < 300 μs, Duty cycle < 2.0%.
3. E_{AS} of 84 mJ is based on starting T_J = 25 °C, L = 1 mH, I_{AS} = 13 A, V_{DD} = 23 V, V_{GS} = 10 V. 100% test at L = 0.3 mH, I_{AS} = 20 A.
4. As an N-ch device, the negative Vgs rating is for low duty cycle pulse ocurrence only. No continuous rating is implied.
5. $I_{SD} \le 22.5$ A, di/dt ≤ 200 A/μs, $V_{DD} \le BV_{DSS}$, Starting T_J = 25 °C.

Typical Characteristics T_J = 25 °C unless otherwise noted

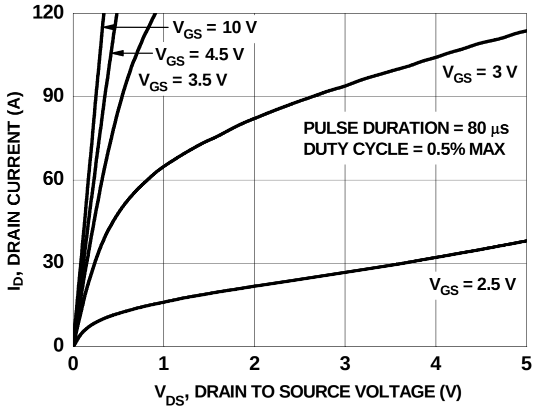


Figure 1. On-Region Characteristics

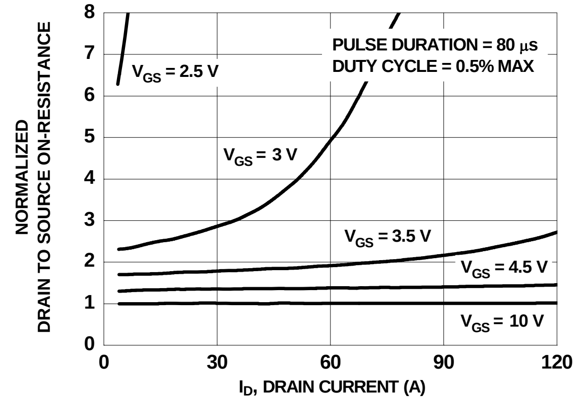


Figure 2. Normalized On-Resistance vs Drain Current and Gate Voltage

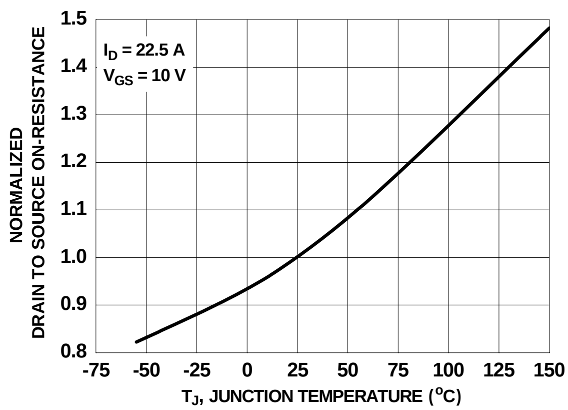


Figure 3. Normalized On-Resistance vs Junction Temperature

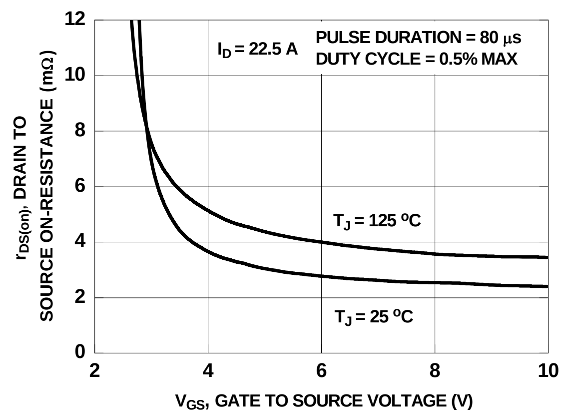


Figure 4. On-Resistance vs Gate to Source Voltage

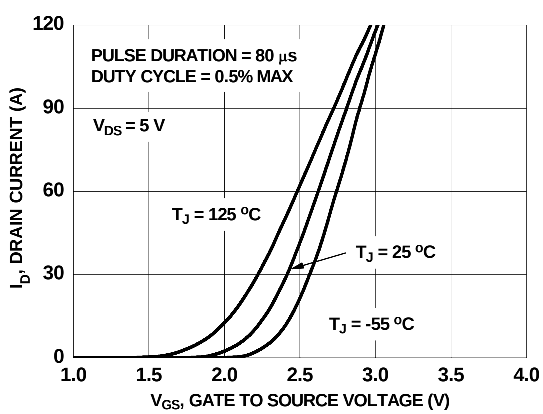


Figure 5. Transfer Characteristics

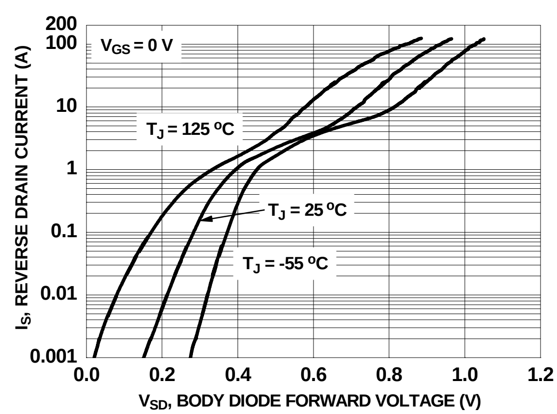


Figure 6. Source to Drain Diode Forward Voltage vs Source Current

Typical Characteristics T_J = 25 °C unless otherwise noted

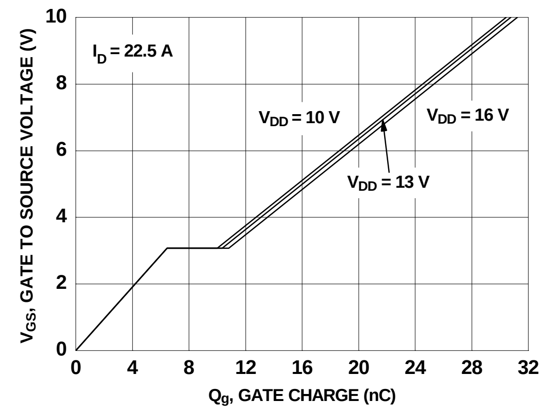


Figure 7. Gate Charge Characteristics

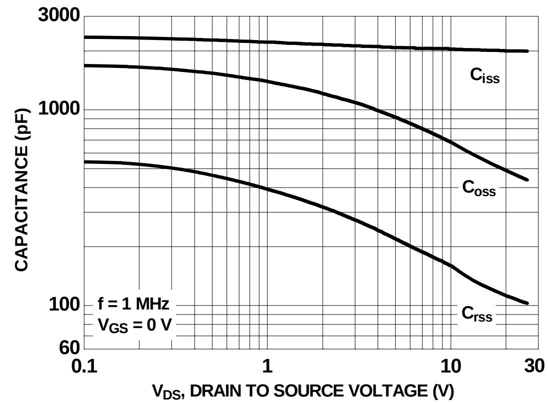


Figure 8. Capacitance vs Drain to Source Voltage

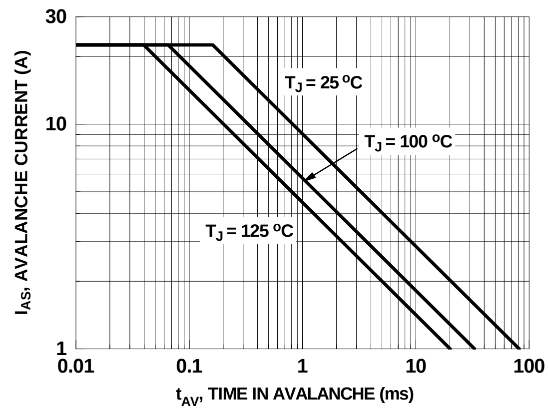


Figure 9. Unclamped Inductive Switching Capability

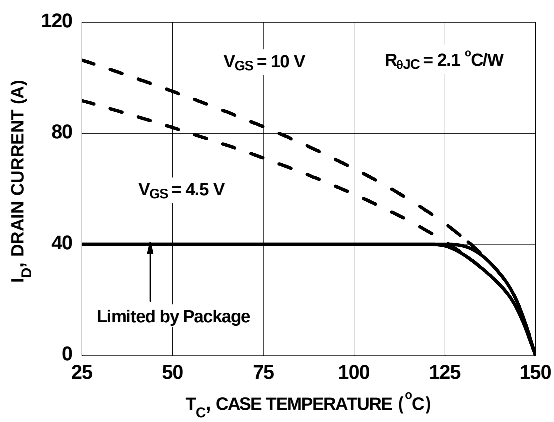


Figure 10. Maximum Continuous Drain Current vs Case Temperature

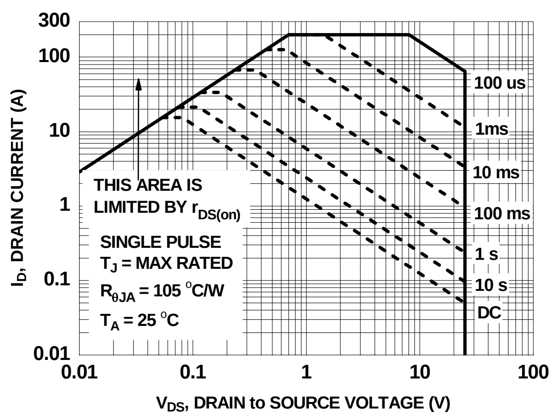


Figure 11. Forward Bias Safe Operating Area

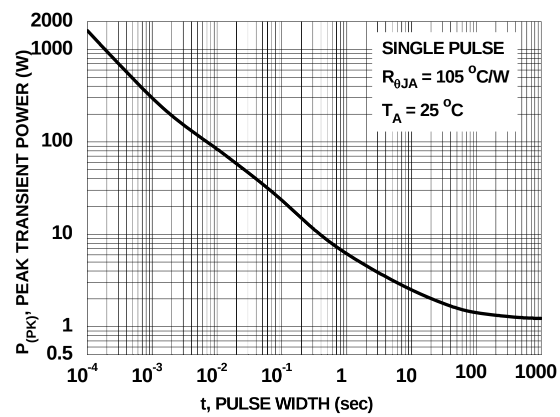


Figure 12. Single Pulse Maximum Power Dissipation

Typical Characteristics T_J = 25 °C unless otherwise noted

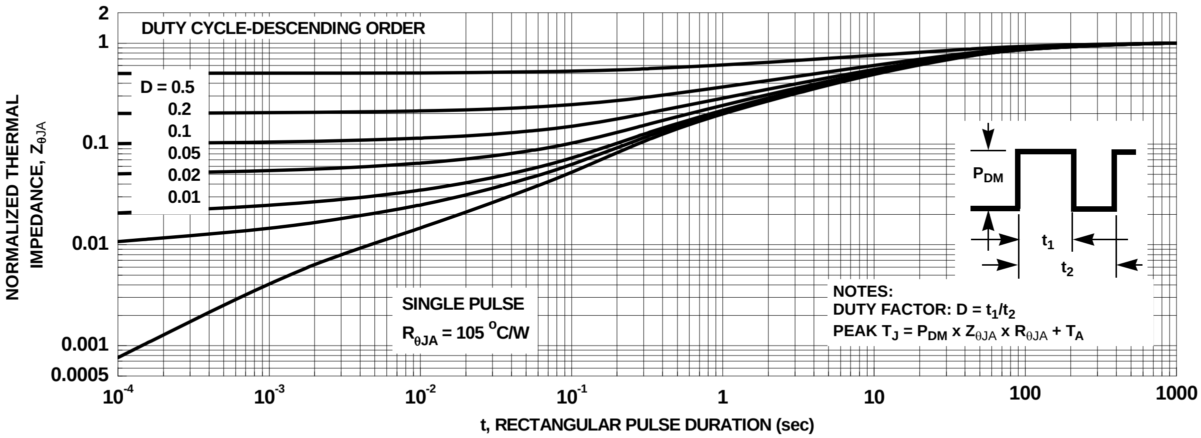


Figure 13. Junction-to-Ambient Transient Thermal Response Curve

Typical Characteristics (continued)

SyncFET Schottky body diode Characteristics

ON Semiconductor's SyncFET process embeds a Schottky diode in parallel with PowerTrench MOSFET. This diode exhibits similar characteristics to a discrete external Schottky diode in parallel with a MOSFET. Figure 13 shows the reverse recovery characteristic of the FDMC2514SDC.

Schottky barrier diodes exhibit significant leakage at high temperature and high reverse voltage. This will increase the power in the device.

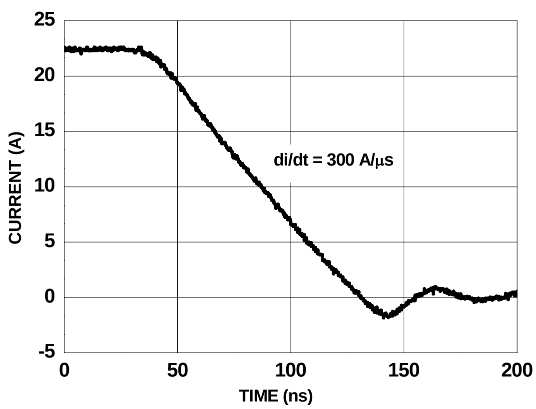


Figure 13. FDMC2514SDC SyncFET body diode reverse recovery characteristic

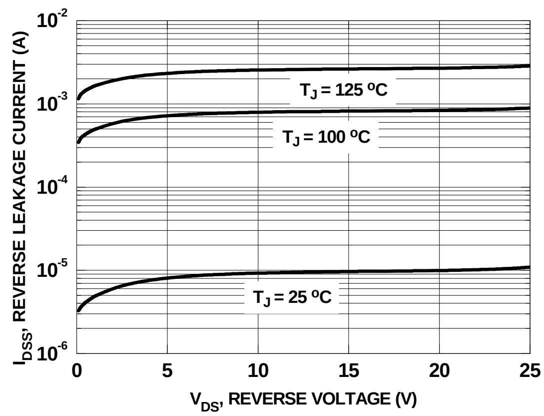


Figure 14. SyncFET body diode reverse leakage versus drain-source voltage

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:
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